



STH240N75F3-2, STH240N75F3-6

N-channel 75 V, 2.6 mΩ typ., 180 A STripFET™ III Power MOSFET in H²PAK-2 and H²PAK-6 packages

Datasheet — production data

Features

Order code	V _{DSS}	R _{DS(on)} max.	I _D
STH240N75F3-2	75 V	< 3.0 mΩ	180 A
STH240N75F3-6			

- Conduction losses reduced
- Low profile, very low parasitic inductance

Applications

- Switching application

Description

These devices are N-channel enhancement mode Power MOSFETs produced using STMicroelectronics' STripFET™ III technology, which is specifically designed to minimize on-resistance and gate charge to provide superior switching performance.

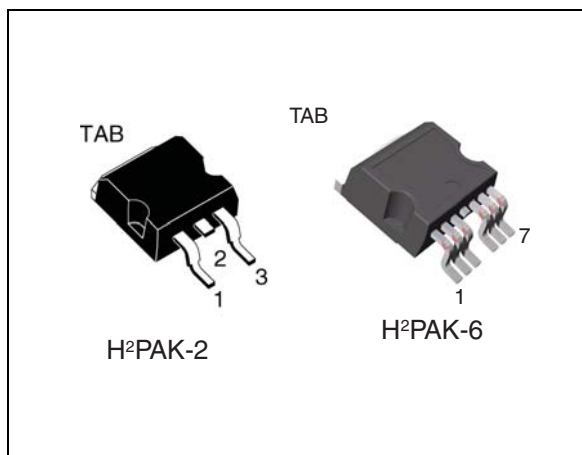


Figure 1. Internal schematic diagram

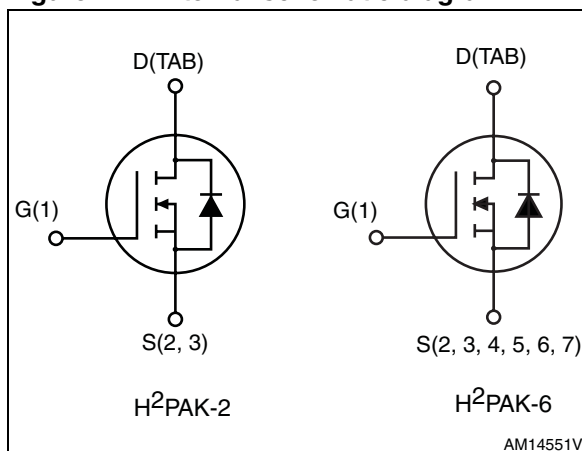


Table 1. Device summary

Order code	Marking	Package	Packaging
STH240N75F3-2	240N75F3	H ² PAK-2	Tape and reel
STH240N75F3-6		H ² PAK-6	

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1 Electrical ratings

Table 2. Absolute maximum ratings

Symbol	Parameter	Value	Unit
V_{DS}	Drain-source voltage	75	V
V_{GS}	Gate-source voltage	± 20	V
$I_D^{(1)}$	Drain current (continuous) at $T_C = 25\text{ }^\circ\text{C}$	180	A
I_D	Drain current (continuous) at $T_C = 100\text{ }^\circ\text{C}$	170	A
$I_{DM}^{(2)}$	Drain current (pulsed)	720	A
P_{TOT}	Total dissipation at $T_C = 25\text{ }^\circ\text{C}$	300	W
	Derating factor	2	W/ $^\circ\text{C}$
$E_{AS}^{(3)}$	Single pulse avalanche energy	600	mJ
T_{stg}	Storage temperature	-55 to 175	$^\circ\text{C}$
T_j	Operating junction temperature		

1. Current limited by package.
2. Pulse width limited by safe operating area.
3. Starting $T_j = 25\text{ }^\circ\text{C}$, $I_D = 60\text{ A}$, $V_{DD} = 15\text{ V}$.

Table 3. Thermal data

Symbol	Parameter	Value	Unit
$R_{thj-case}$	Thermal resistance junction-case max	0.5	$^\circ\text{C/W}$
$R_{thj-pcb}^{(1)}$	Thermal resistance junction-pcb max	35	$^\circ\text{C/W}$

1. When mounted on 1 inch² FR-4 2 oz Cu.

2 Electrical characteristics

(T_{case} = 25 °C unless otherwise specified)

Table 4. On /off states

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source breakdown voltage	$I_D = 250 \mu A$, $V_{GS} = 0$	75			V
I_{DSS}	Zero gate voltage drain current	$V_{DS} = 75 V$, $V_{DS} = 75 V$, $T_C = 125 ^\circ C$, $V_{GS} = 0$			10 100	μA μA
I_{GSS}	Gate body leakage current	$V_{DS} = \pm 20 V$, $V_{DS} = 0$			± 200	nA
$V_{GS(th)}$	Gate threshold voltage	$V_{DS} = V_{GS}$, $I_D = 250 \mu A$	2		4	V
$R_{DS(on)}$	Static drain-source on-resistance	$V_{GS} = 10 V$, $I_D = 90 A$		2.6	3.0	m Ω

Table 5. Dynamic

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
C_{iss}	Input capacitance	$V_{DS} = 25 V$, $f = 1 MHz$, $V_{GS} = 0$	-	6800	-	pF
C_{oss}	Output capacitance			1100		pF
C_{rss}	Reverse transfer capacitance			50		pF
Q_g	Total gate charge	$V_{DD} = 37.5 V$, $I_D = 120 A$,	-	87	-	nC
Q_{gs}	Gate-source charge	$V_{GS} = 10 V$		30		nC
Q_{gd}	Gate-drain charge	(see Figure 14)		26		nC

Table 6. Switching times

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-on delay time	$V_{DD} = 37.5 V$, $I_D = 60 A$ $R_G = 4.7 \Omega$, $V_{GS} = 10 V$, (see Figure 13)	-	25	-	ns
t_r	Rise time			70		ns
$t_{d(off)}$	Turn-off delay time		-	100	-	ns
t_f	Fall time			15		ns

Table 7. Source drain diode

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
I_{SD}	Source-drain current		-		180	A
$I_{SD}^{(1)}$	Source-drain current (pulsed)		-		720	A
$V_{SD}^{(2)}$	Forward on voltage	$I_{SD} = 120\text{ A}$, $V_{GS} = 0$	-		1.5	V
t_{rr}	Reverse recovery time	$I_{SD} = 120\text{ A}$, $di/dt = 100\text{ A}/\mu\text{s}$	-	80		ns
Q_{rr}	Reverse recovery charge	$V_{DD} = 30\text{ V}$, $T_j = 150\text{ }^\circ\text{C}$	-	180		nC
I_{RRM}	Reverse recovery current	(see Figure 15)	-	4.5		A

1. Pulse width limited by safe operating area.
2. Pulsed: Pulse duration = 300 μs , duty cycle 1.5%.

2.1 Electrical characteristics (curves)

Figure 2. Safe operating area

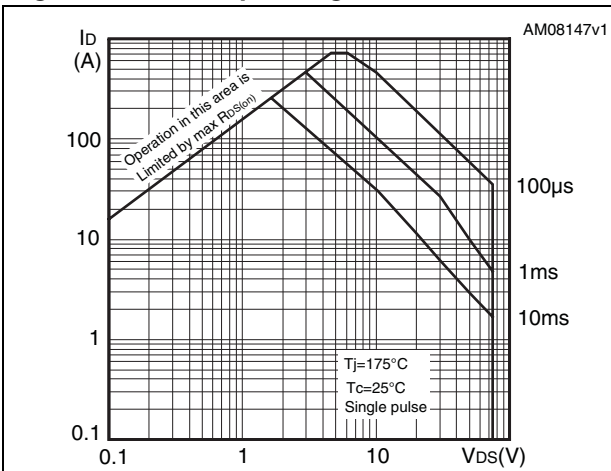


Figure 3. Thermal impedance

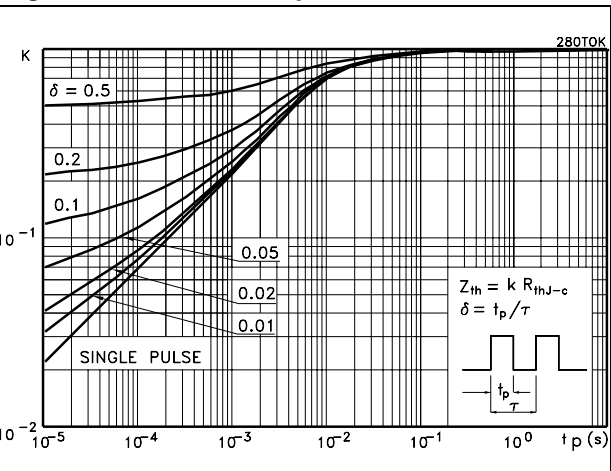


Figure 4. Output characteristics

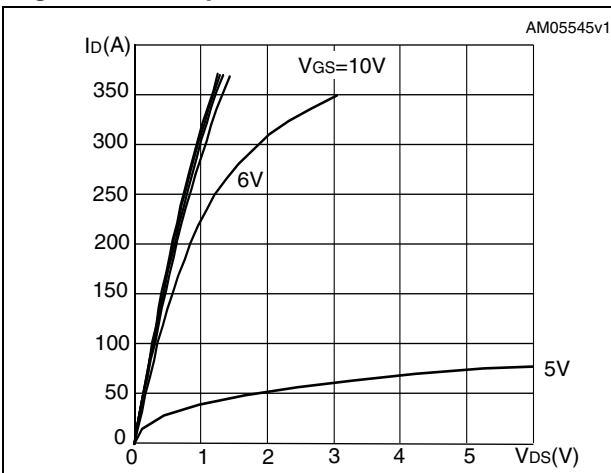


Figure 5. Transfer characteristics

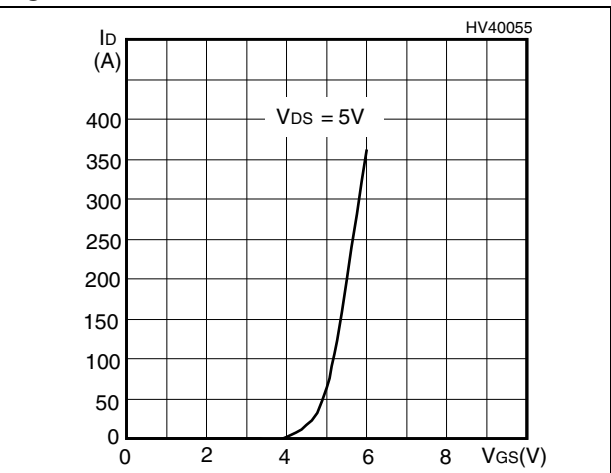


Figure 6. Normalized BV_{DSS} vs temperature

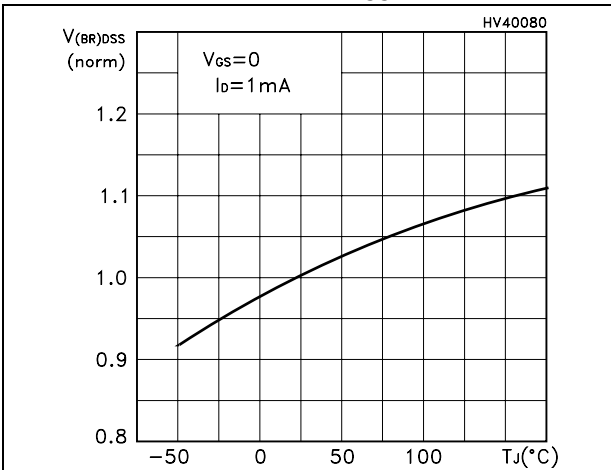


Figure 7. Static drain-source on-resistance

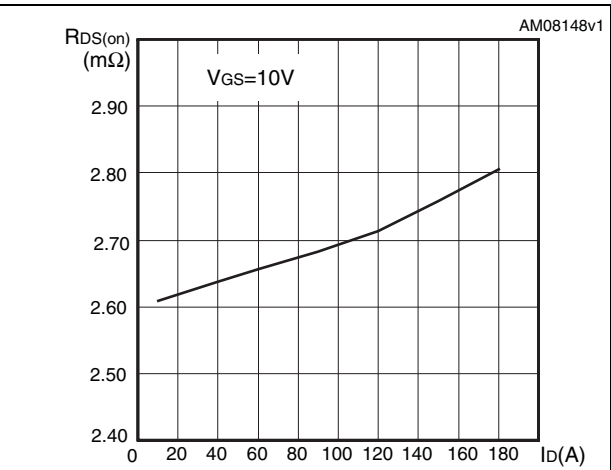


Figure 8. Gate charge vs gate-source voltage

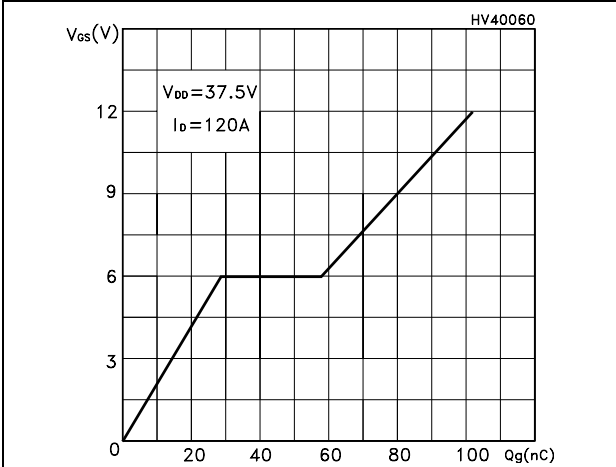


Figure 9. Capacitance variations

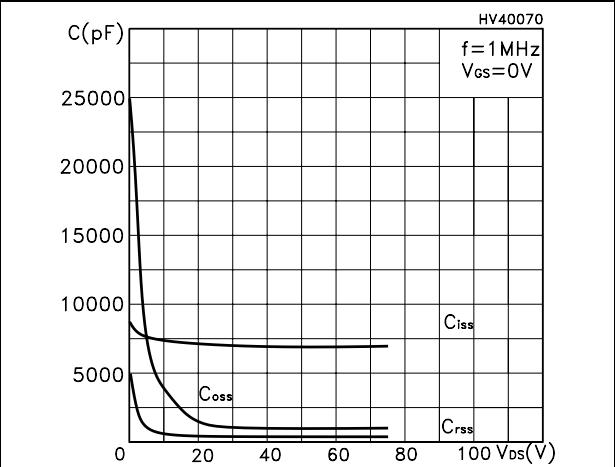


Figure 10. Normalized gate threshold voltage vs temperature

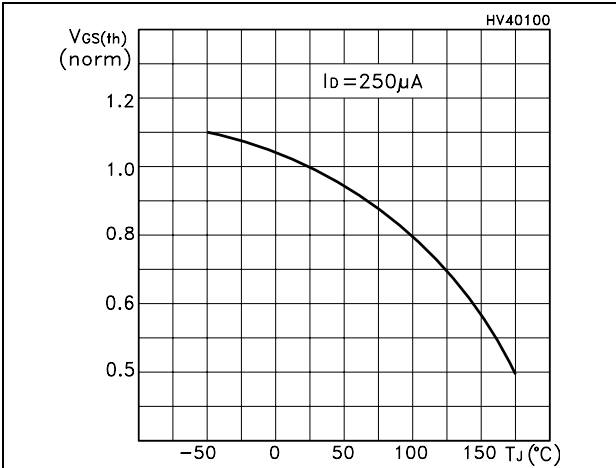


Figure 11. Normalized on-resistance vs temperature

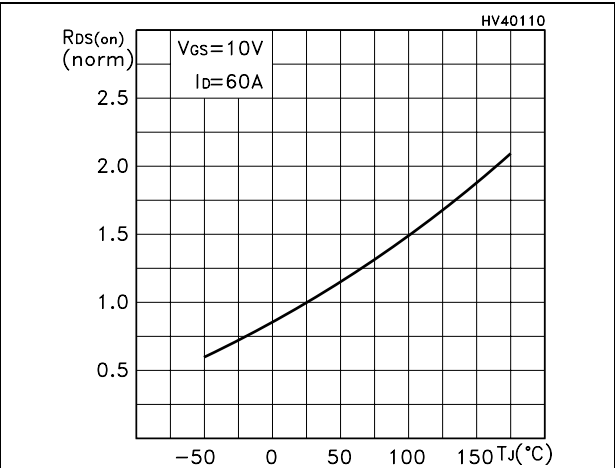
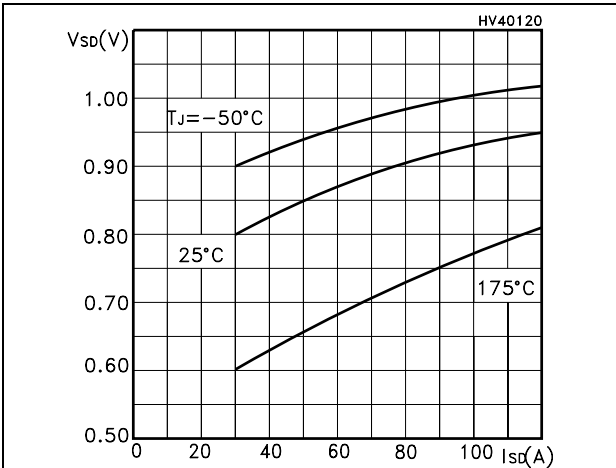


Figure 12. Source-drain diode forward characteristics



3 Test circuits

Figure 13. Switching times test circuit for resistive load

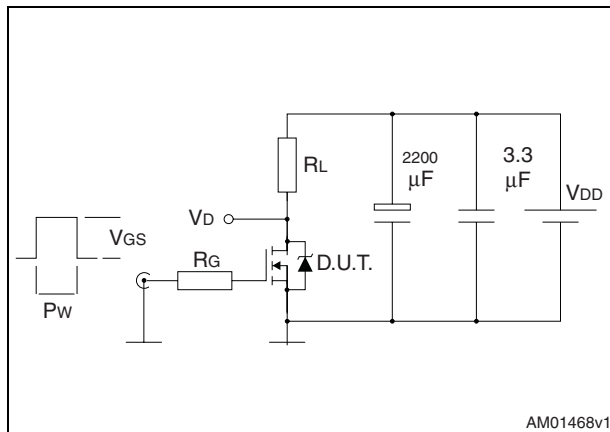


Figure 14. Gate charge test circuit

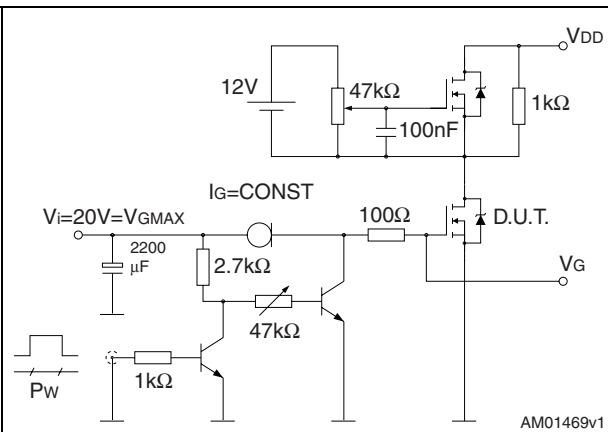


Figure 15. Test circuit for inductive load switching and diode recovery times

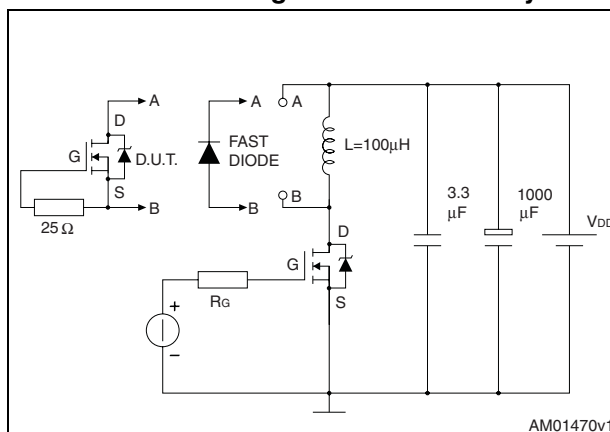


Figure 16. Unclamped inductive load test circuit

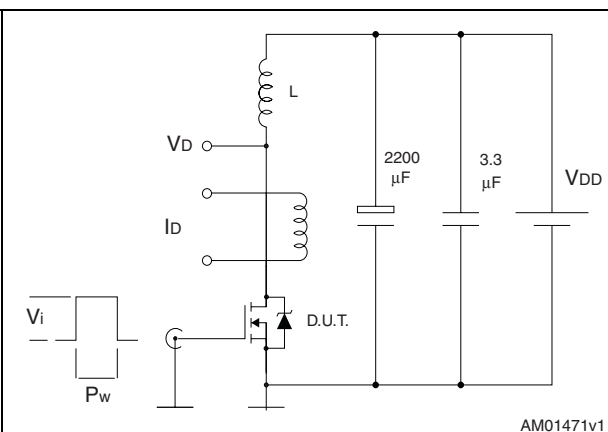


Figure 17. Unclamped inductive waveform

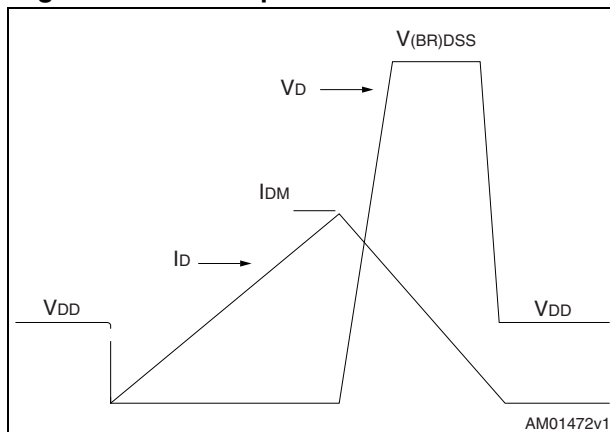
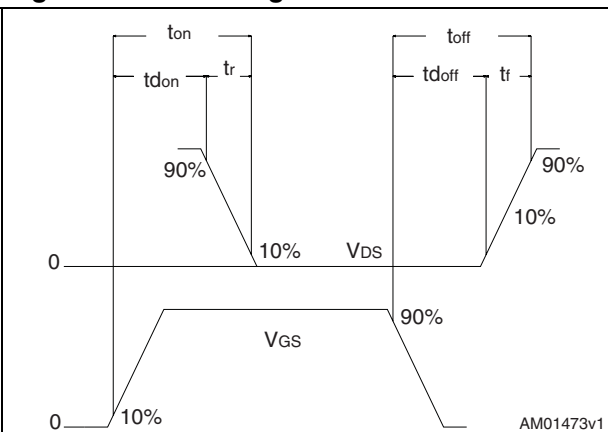


Figure 18. Switching time waveform



4 Package mechanical data

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK® packages, depending on their level of environmental compliance. ECOPACK® specifications, grade definitions and product status are available at: www.st.com. ECOPACK® is an ST trademark.

Table 8. H²PAK-2 mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	4.30	-	4.80
A1	0.03		0.20
C	1.17		1.37
e	4.98		5.18
E	0.50		0.90
F	0.78		0.85
H	10.00		10.40
H1	7.40		7.80
L	15.30		15.80
L1	1.27		1.40
L2	4.93		5.23
L3	6.85		7.25
L4	1.5		1.7
M	2.6		2.9
R	0.20		0.60
V	0°		8°

Figure 19. H²PAK-2 drawing

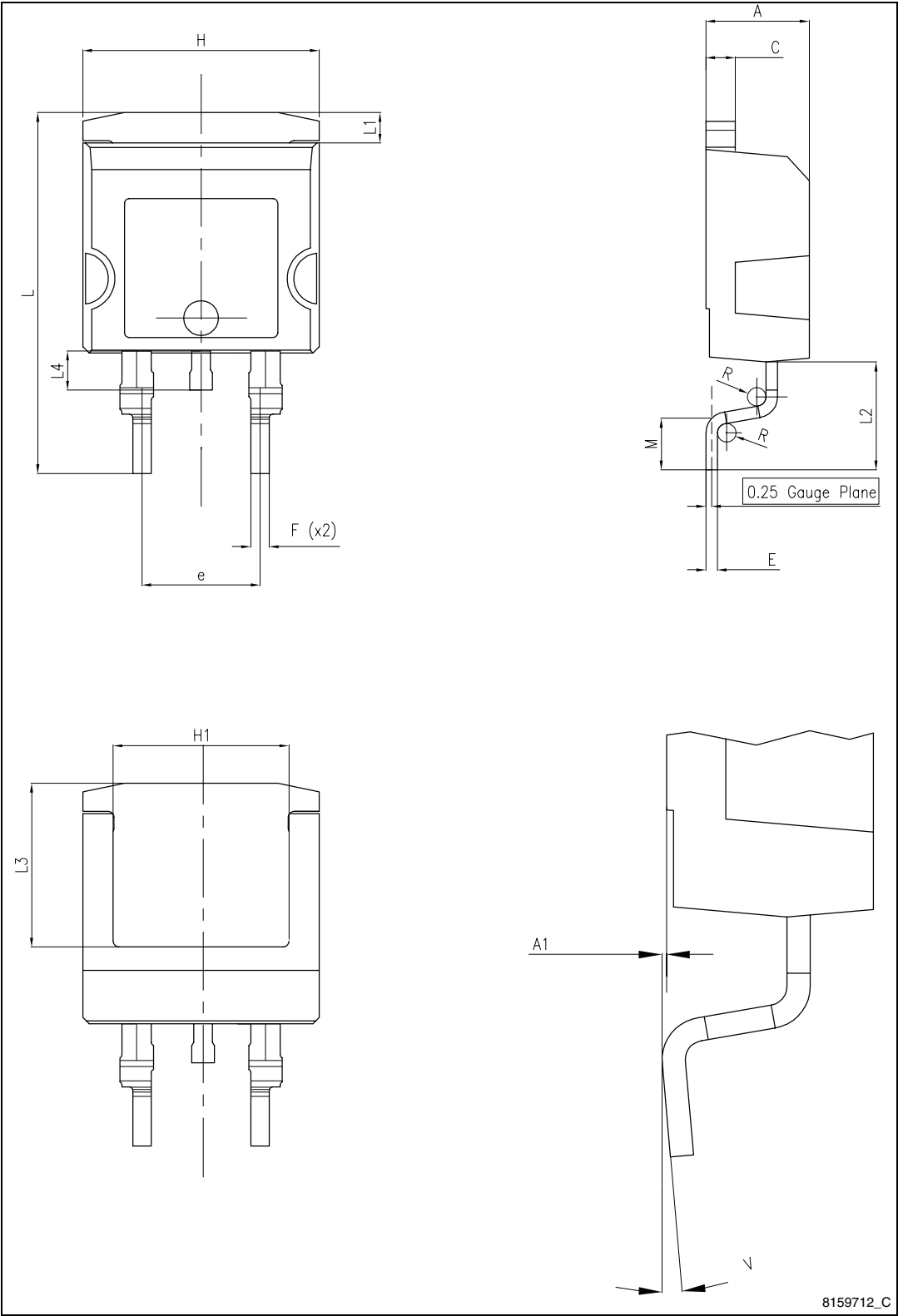


Figure 20. H²PAK-2 recommended footprint (dimensions in mm)

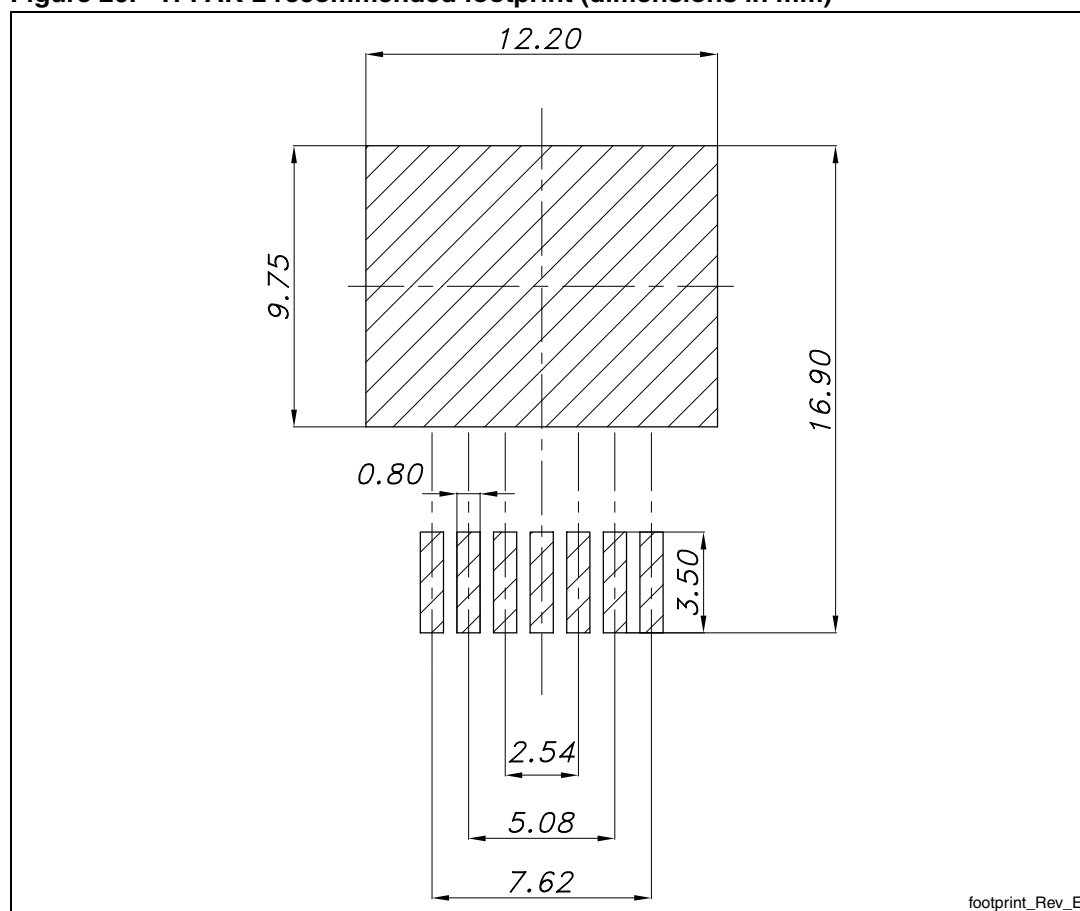


Table 9. H²PAK-6 mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	4.30	-	4.80
A1	0.03		0.20
C	1.17		1.37
e	2.34		2.74
e1	4.88		5.28
e2	7.42		7.82
E	0.45		0.60
F	0.50		0.70
H	10.00		10.40
H1	7.40		7.80
L	14.75		15.25
L1	1.27		1.40
L2	4.35		4.95
L3	6.85		7.25
L4	1.5		1.75
M	1.90		2.50
R	0.20		0.60
V	0°		8°

Figure 21. H²PAK-6 drawing

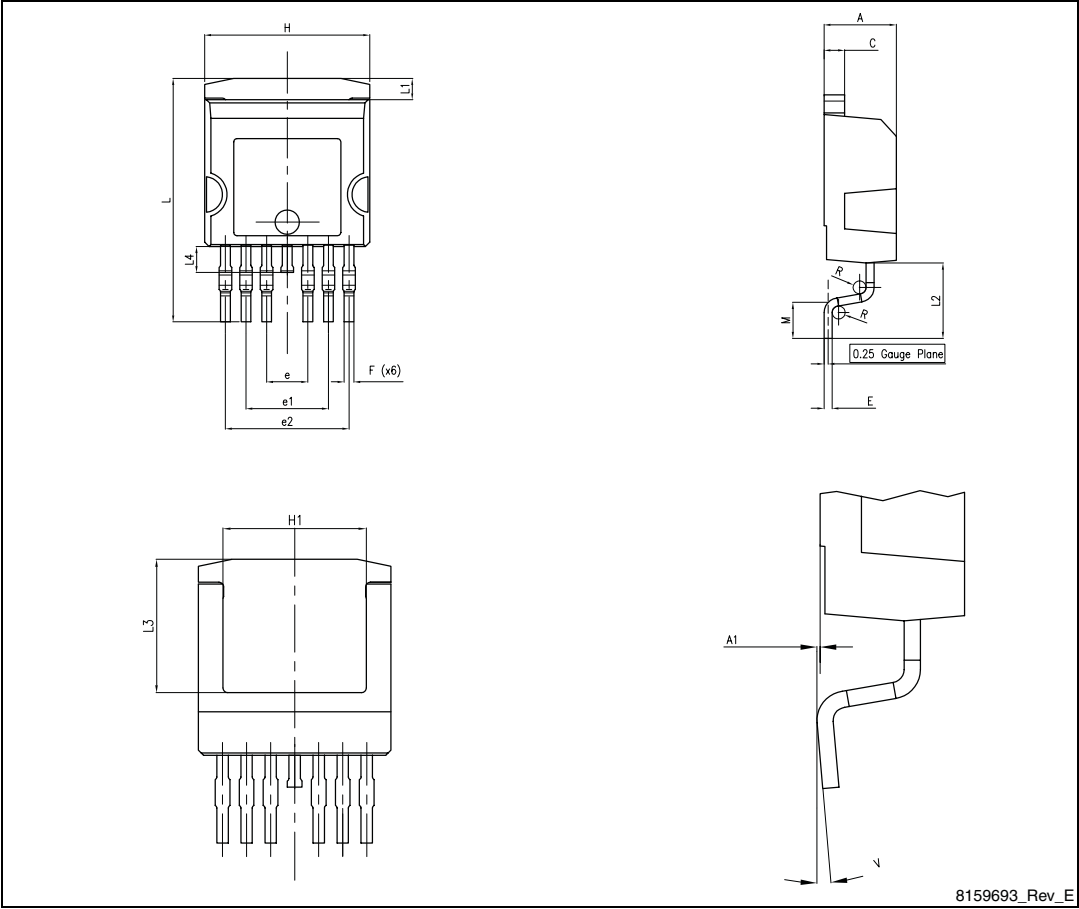
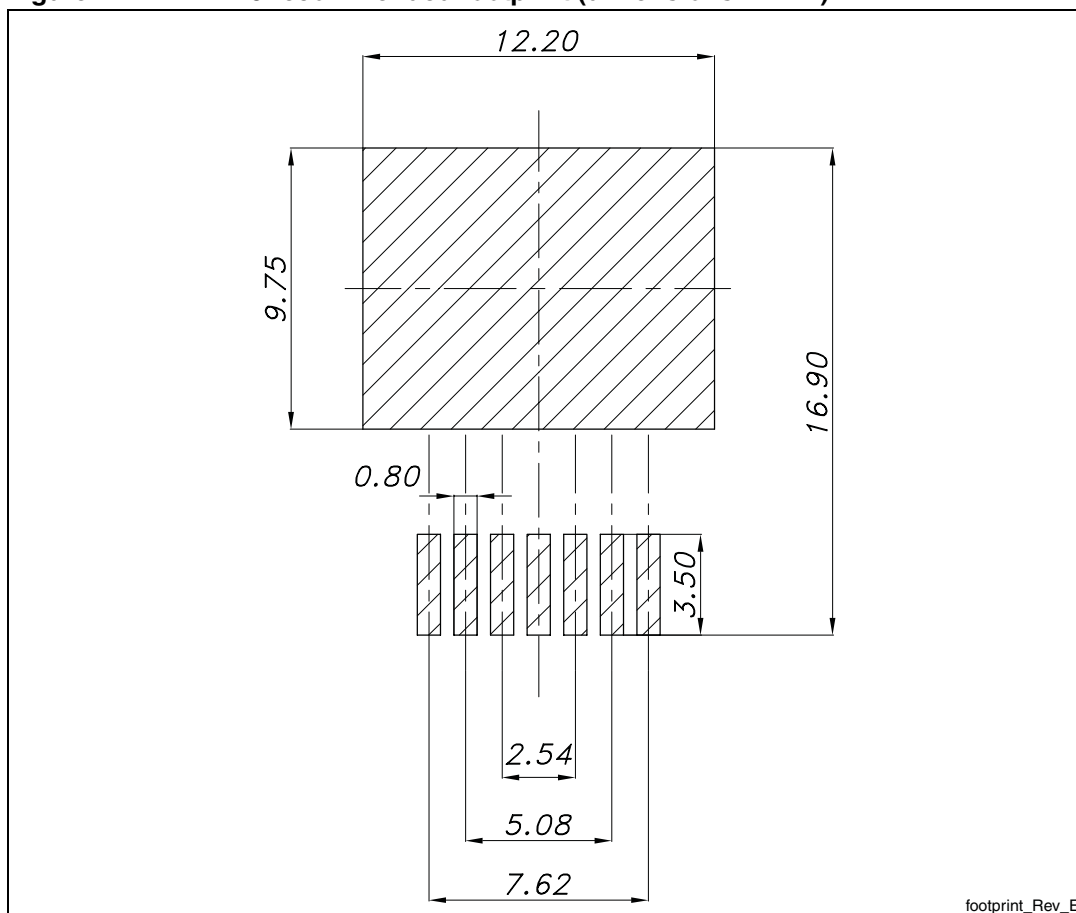


Figure 22. H²PAK-6 recommended footprint (dimensions in mm)

5 Packaging mechanical data

Table 10. H²PAK-2 and H²PAK-6 tape and reel mechanical data

Tape			Reel		
Dim.	mm		Dim.	mm	
	Min.	Max.		Min.	Max.
A0	10.5	10.7	A		330
B0	15.7	15.9	B	1.5	
D	1.5	1.6	C	12.8	13.2
D1	1.59	1.61	D	20.2	
E	1.65	1.85	G	24.4	26.4
F	11.4	11.6	N	100	
K0	4.8	5.0	T		30.4
P0	3.9	4.1			
P1	11.9	12.1	Base qty		1000
P2	1.9	2.1	Bulk qty		1000
R	50				
T	0.25	0.35			
W	23.7	24.3			

Figure 23. Tape

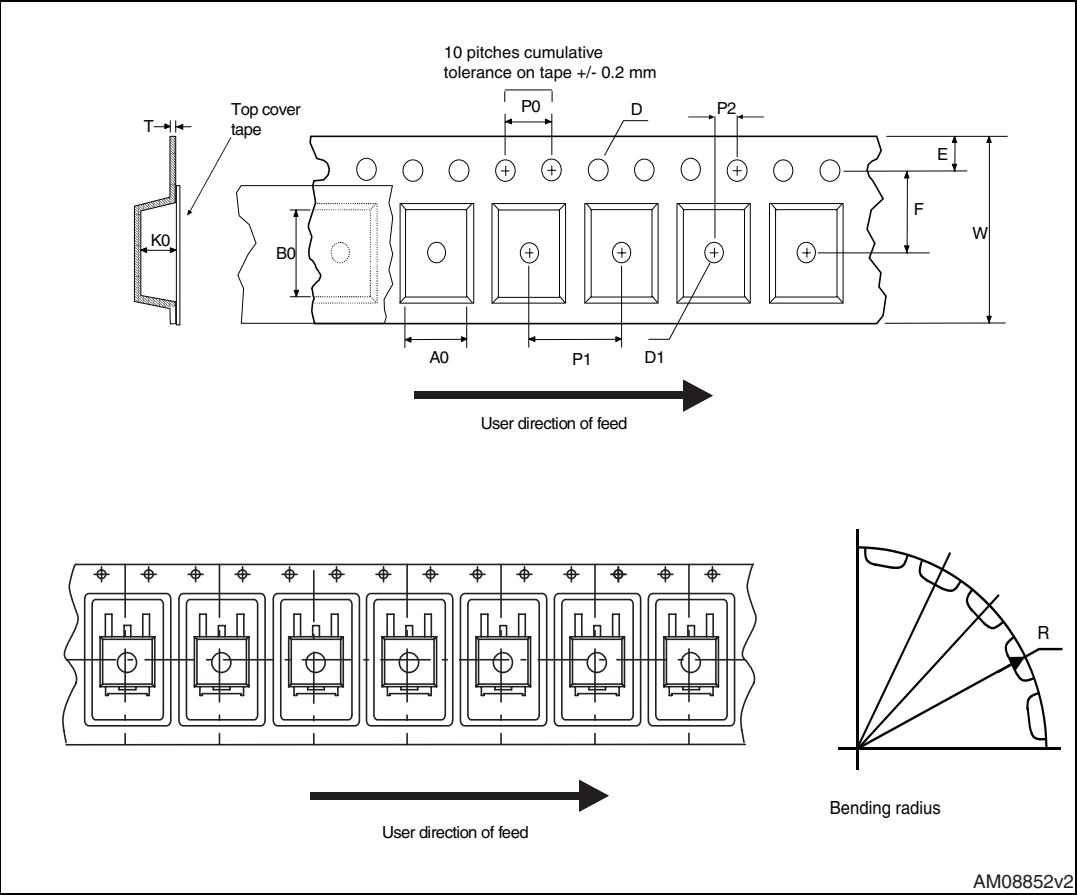
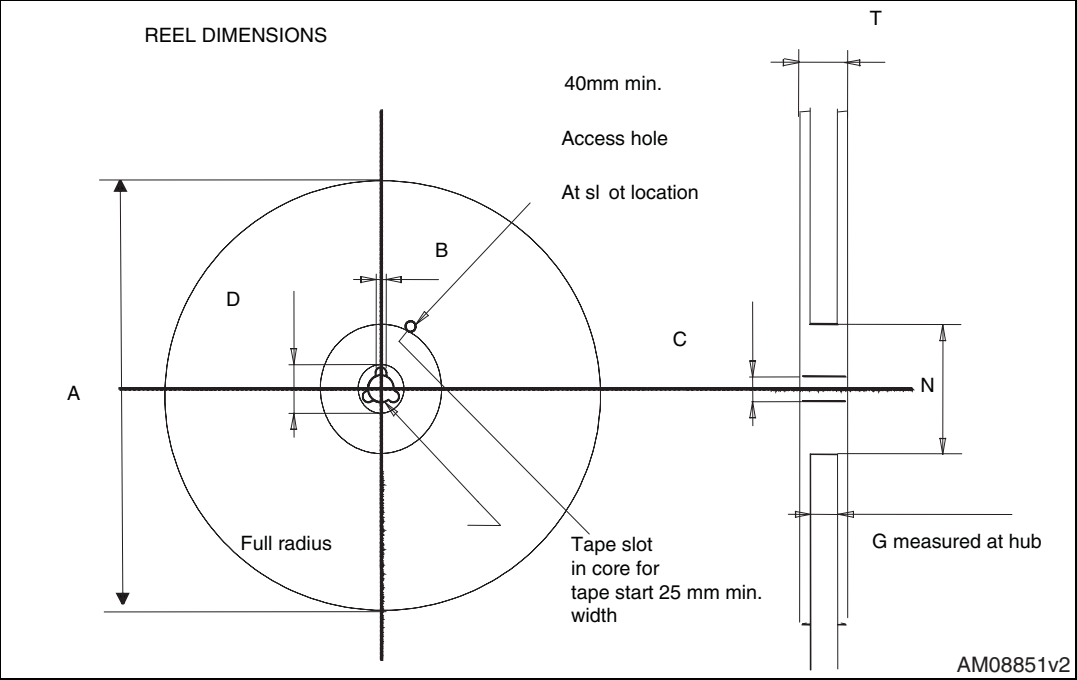


Figure 24. Reel



6 Revision history

Table 11. Document revision history

Date	Revision	Changes
19-Oct-2011	1	Initial release.
02-Jul-2012	2	Added new device in H ² PAK-2. <i>Table 1: Device summary</i> has been modified accordingly. <i>Table 8: H²PAK-2 mechanical data</i> , <i>Figure 19: H²PAK-2 drawing</i> and <i>Figure 20: H²PAK-2 recommended footprint (dimensions in mm)</i> have been added. Minor text changes.

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